Robin John Nicholas

List of Publications by Year in Descending Order

315 papers	13,496 citations	52 h-index	107 g-index
320 ext. papers	14,473 ext. citations	4.6 avg, IF	6.16 L-index

#	Paper	IF	Citations
315	Chemical Interaction at the MoO/CHNHPbICl Interface. *ACS Applied Materials & Interfaces*, **2021**, 13, 17085-17092	9.5	4
314	Filamentary High-Resolution Electrical Probes for Nanoengineering. *Nano Letters*, **2020**, 20, 1067-1073	11.5	2
313	Giant Fine Structure Splitting of the Bright Exciton in a Bulk MAPbBr Single Crystal. *Nano Letters*, **2019**, 19, 7054-7061	11.5	23
312	Solubilization of Carbon Nanotubes with Ethylene-Vinyl Acetate for Solution-Processed Conductive Films and Charge Extraction Layers in Perovskite Solar Cells. *ACS Applied Materials & Interfaces*, **2019**, 11, 1185-1191	9.5	18
311	Structural and Optical Properties of Cs2AgBiBr6 Double Perovskite. *ACS Energy Letters*, **2019**, 4, 299-305	20.1	78
310	Highly Crystalline Methylammonium Lead Tribromide Perovskite Films for Efficient Photovoltaic Devices. *ACS Energy Letters*, **2018**, 3, 1233-1240	20.1	43
309	Multi-band magnetotransport in exfoliated thin films of Cu BiSe. *Journal of Physics Condensed Matter*, **2018**, 30, 155302	1.8	2
308	Carbon Nanotubes for Quantum Dot Photovoltaics with Enhanced Light Management and Charge Transport. *ACS Photonics*, **2018**, 5, 4854-4863	6.3	3
307	Two-Dimensional Excitonic Photoluminescence in Graphene on a Cu Surface. *ACS Nano*, **2017**, 11, 3207-3213	13.2	9
306	Dopant-Free Planar n□p Perovskite Solar Cells with Steady-State Efficiencies Exceeding 18%. *ACS Energy Letters*, **2017**, 2, 622-628	20.1	58
305	Spatially resolved studies of the phases and morphology of methylammonium and formamidinium lead tri-halide perovskites. *Nanoscale*, **2017**, 9, 3222-3230	7.7	36
304	Unraveling the Exciton Binding Energy and the Dielectric Constant in Single-Crystal Methylammonium Lead Triiodide Perovskite. *Journal of Physical Chemistry Letters*, **2017**, 8, 1851-1855	6.4	108
303	Impact of microstructure on the electron□hole interaction in lead halide perovskites. *Energy and Environmental Science*, **2017**, 10, 1358-1366	35.4	31
302	Investigating the Role of 4-Tert Butylpyridine in Perovskite Solar Cells. *Advanced Energy Materials*, **2017**, 7, 1601079	21.8	76
301	A low viscosity, low boiling point, clean solvent system for the rapid crystallisation of highly specular perovskite films. *Energy and Environmental Science*, **2017**, 10, 145-152	35.4	253
300	Quantum dot-like excitonic behavior in individual single walled-carbon nanotubes. *Scientific Reports* , **2016**, 6, 37167	4.9	4
299	Efficient perovskite solar cells by metal ion doping. *Energy and Environmental Science*, **2016**, 9, 2892-2901	35.4	301

298	The Impact of Phase Retention on the Structural and Optoelectronic Properties of Metal Halide Perovskites. *Advanced Materials*, **2016**, 28, 10757-10763	24	52
297	Structured Organic-Inorganic Perovskite toward a Distributed Feedback Laser. *Advanced Materials*, **2016**, 28, 923-9	24	209
296	Determination of the exciton binding energy and effective masses for methylammonium and formamidinium lead tri-halide perovskite semiconductors. *Energy and Environmental Science*, **2016**, 9, 962-970	35.4	457
295	Independence of optical absorption on Auger ionization in single-walled carbon nanotubes revealed by ultrafast e photodoping. *New Journal of Physics*, **2016**, 18, 023051	2.9	
294	Research Update: Strategies for improving the stability of perovskite solar cells. *APL Materials*, **2016**, 4, 091503	5.7	106
293	Thiophene-based dyes for probing membranes. *Organic and Biomolecular Chemistry*, **2015**, 13, 3792-802	3.9	33
292	Hot carrier relaxation of Dirac fermions in bilayer epitaxial graphene. *Journal of Physics Condensed Matter*, **2015**, 27, 164202	1.8	17
291	Rapid epitaxy-free graphene synthesis on silicidated polycrystalline platinum. *Nature Communications*, **2015**, 6, 7536	17.4	45
290	Direct measurement of the exciton binding energy and effective masses for charge carriers in organic horganic tri-halide perovskites. *Nature Physics*, **2015**, 11, 582-587	16.2	1282
289	Reduced Stark shift in three-dimensionally confined GaN/AlGaN asymmetric multi-quantum disks. *Optical Materials Express*, **2015**, 5, 849	2.6	2
288	Surface-Effect-Induced Optical Bandgap Shrinkage in GaN Nanotubes. *Nano Letters*, **2015**, 15, 4472-6	11.5	17
287	Low-temperature processed electron collection layers of graphene/TiO2 nanocomposites in thin film perovskite solar cells. *Nano Letters*, **2014**, 14, 724-30	11.5	917
286	Enhanced Hole Extraction in Perovskite Solar Cells Through Carbon Nanotubes. *Journal of Physical Chemistry Letters*, **2014**, 5, 4207-12	6.4	126
285	Carbon nanotube/polymer composites as a highly stable hole collection layer in perovskite solar cells. *Nano Letters*, **2014**, 14, 5561-8	11.5	944
284	Hyperspectral imaging of exciton photoluminescence in individual carbon nanotubes controlled by high magnetic fields. *Nano Letters*, **2014**, 14, 5194-200	11.5	15
283	An ultrafast carbon nanotube terahertz polarisation modulator. *Journal of Applied Physics*, **2014**, 115, 203108	2.5	25
282	Engineering nanostructures by binding single molecules to single-walled carbon nanotubes. *ACS Nano*, **2014**, 8, 12748-54	16.7	9
281	Beyond 100 Tesla: Scientific experiments using single-turn coils. *Comptes Rendus Physique*, **2013**, 14, 115-120	1.4	6

280	Production of high-purity single-chirality carbon nanotube hybrids by selective polymer exchange. *Small*, **2013**, 9, 2245-9	11	21
279	Extreme sensitivity of graphene photoconductivity to environmental gases. *Nature Communications*, **2012**, 3, 1228	17.4	94
278	Nanoengineering coaxial carbon nanotube-dual-polymer heterostructures. *ACS Nano*, **2012**, 6, 6058-66	16.7	32
277	Electronic and mechanical modification of single-walled carbon nanotubes by binding to porphyrin oligomers. *ACS Nano*, **2011**, 5, 2307-15	16.7	47
276	Noncovalent Binding of Carbon Nanotubes by Porphyrin Oligomers. *Angewandte Chemie*, **2011**, 123, 2361-2364	3.6	10
275	Noncovalent binding of carbon nanotubes by porphyrin oligomers. *Angewandte Chemie - International Edition*, **2011**, 50, 2313-6	16.4	85
274	Ultrafast charge separation at a polymer-single-walled carbon nanotube molecular junction. *Nano Letters*, **2011**, 11, 66-72	11.5	76
273	Ultrafast Charge Separation at a Single-walled Carbon Nanotube Polymer Interface. *Materials Research Society Symposia Proceedings*, **2011**, 1286, 7		
272	UV vis absorption spectroscopy of carbon nanotubes: Relationship between the electron plasmon and nanotube diameter. *Chemical Physics Letters*, **2010**, 493, 19-23	2.5	124
271	BAND STRUCTURE AND ELECTRON VELOCITY MEASUREMENT IN CARBON NANOTUBES AND GRAPHENE. *International Journal of Modern Physics B*, **2009**, 23, 2655-2664	1.1	1
270	Terahertz Excitonic Response of Isolated Single-Walled Carbon Nanotubes. *Journal of Physical Chemistry C*, **2009**, 113, 18106-18109	3.8	34
269	Observation of a type II heterojunction in a highly ordered polymer-carbon nanotube nanohybrid structure. *Nano Letters*, **2009**, 9, 3871-6	11.5	71
268	Cyclotron resonance of electrons and holes in graphene monolayers. *Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences*, **2008**, 366, 237-43	3	13
267	Introduction. Carbon-based electronics: fundamentals and device applications. *Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences*, **2008**, 366, 189-93	3	21
266	Direct spectroscopic evidence of energy transfer from photo-excited semiconducting polymers to single-walled carbon nanotubes. *Nanotechnology*, **2008**, 19, 095603	3.4	54
265	Investigation of InGaAsP-based solar cells for double-junction photovoltaic devices. *Thin Solid Films*, **2008**, 516, 6744-6747	2.2	5
264	Polymer structure and solvent effects on the selective dispersion of single-walled carbon nanotubes. *Journal of the American Chemical Society*, **2008**, 130, 3543-53	16.4	264
263	Highly selective dispersion of single-walled carbon nanotubes using aromatic polymers. *Nature Nanotechnology*, **2007**, 2, 640-6	28.7	880

262	Temperature-dependent cyclotron resonance in a hybridized electron–hole system in InAs/GaSb heterostructures. *Semiconductor Science and Technology*, **2007**, 22, 194-202	1.8	7
261	High Magnetic Field Phenomena in Carbon Nanotubes. *Topics in Applied Physics*, **2007**, 393-422	0.5	11
260	Current-driven breakdown of the quantized Hall states of a broken-gap 2D electron–hole system. *Semiconductor Science and Technology*, **2006**, 21, 1758-1763	1.8	1
259	Temperature induced restoration of fluorescence from oxidised single-walled carbon nanotubes in aqueous sodium dodecylsulfate solution. *Physical Chemistry Chemical Physics*, **2006**, 8, 3547-51	3.6	31
258	The effects of nitrogen and boron doping on the optical emission and diameters of single-walled carbon nanotubes. *Carbon*, **2006**, 44, 2752-2757	10.4	51
257	Chirality-dependent boron-mediated growth of nitrogen-doped single-walled carbon nanotubes. *Physical Review B*, **2005**, 72,	3.3	31
256	Comparative study of photoluminescence of single-walled carbon nanotubes wrapped with sodium dodecyl sulfate, surfactin and polyvinylpyrrolidone. *Nanotechnology*, **2005**, 16, S202-S205	3.4	46
255	Magnetic separation of Fe catalyst from single-walled carbon nanotubes in an aqueous surfactant solution. *Carbon*, **2005**, 43, 1151-1155	10.4	26
254	Diameter-selective encapsulation of metallocenes in single-walled carbon nanotubes. *Nature Materials*, **2005**, 4, 481-5	27	223
253	Bandgap-selective chemical doping of semiconducting single-walled carbon nanotubes. *Nanotechnology*, **2004**, 15, 1844-1847	3.4	14
252	Chirality assignment of single-walled carbon nanotubes with strain. *Physical Review Letters*, **2004**, 93, 156104	7.4	55
251	Mid-infrared electroluminescence from coupled quantum dots and wells. *Journal of Applied Physics*, **2004**, 96, 2725-2730	2.5	
250	Controlled orientation of ellipsoidal fullerene C70 in carbon nanotubes. *Applied Physics Letters*, **2004**, 84, 792-794	3.4	58
249	MAGNETO-PHOTOLUMINESCENCE OF CHIRALITY-CHARACTERIZED SINGLE-WALLED CARBON NANOTUBES. *International Journal of Modern Physics B*, **2004**, 18, 3509-3512	1.1	10
248	Properties of narrow gap quantum dots and wells in the InAs/InSb/GaSb systems. *Physica E: Low-Dimensional Systems and Nanostructures*, **2004**, 20, 204-210	3	13
247	Mid-infrared luminescence from coupled quantum dots and wells. *Physica E: Low-Dimensional Systems and Nanostructures*, **2004**, 21, 341-344	3	2
246	Magnetoresistance studies of strongly coupled superlattices. *Physica E: Low-Dimensional Systems and Nanostructures*, **2004**, 22, 316-319	3	1
245	Far infrared modulated photoluminescence in InSb quantum dots. *Physica E: Low-Dimensional Systems and Nanostructures*, **2004**, 22, 598-602	3	1

244	Comparative studies on acid and thermal based selective purification of HiPCO produced single-walled carbon nanotubes. *Chemical Physics Letters*, **2004**, 386, 239-243	2.5	86
243	Quantum Hall and insulating states of a 2-D electron–hole system. *Physica E: Low-Dimensional Systems and Nanostructures*, **2003**, 20, 160-171	3	4
242	Magneto-photoluminescence studies of a novel quantum dot–quantum well coupled system. *Physica Status Solidi (B): Basic Research*, **2003**, 238, 281-284	1.3	3
241	Spin polarization of 2D electrons in the quantum Hall ferromagnet: evidence for a partially polarized state around filling factor one. *Physica E: Low-Dimensional Systems and Nanostructures*, **2002**, 12, 12-15	3	4
240	Mass enhancement and electron–hole coupling in InAs/GaSb bilayers studied by cyclotron resonance. *Physica E: Low-Dimensional Systems and Nanostructures*, **2002**, 12, 289-292	3	9
239	The quantum Hall effect in an InAs/GaSb based electron–hole system and its current-driven breakdown. *Physica E: Low-Dimensional Systems and Nanostructures*, **2002**, 12, 161-164	3	1
238	Anomalous g-factors and diamagnetic shifts of biexcitons in ZnS quantum wells. *Physica E: Low-Dimensional Systems and Nanostructures*, **2002**, 12, 507-511	3	
237	Tunable mid-IR emission using a novel quantum dot–quantum well coupled system. *Physica E: Low-Dimensional Systems and Nanostructures*, **2002**, 13, 241-245	3	5
236	Magnetoresistance of vertical transport in InAs/GaSb superlattices. *Physica E: Low-Dimensional Systems and Nanostructures*, **2002**, 13, 736-740	3	
235	Magnetic-field-induced suppression of tunnelling into a two-dimensional electron system. *Journal of Physics Condensed Matter*, **2002**, 14, 5561-5574	1.8	2
234	InGaAs/GaAs quantum wells and quantum dots on (111)B orientation. *Solid State Communications*, **2001**, 117, 649-654	1.6	1
233	Breakdown of the quantum Hall effect in an electron–hole system. *Physica B: Condensed Matter*, **2001**, 298, 8-12	2.8	8
232	Edge effects in an insulating state of an electron–hole system in magnetic field. *Physica B: Condensed Matter*, **2001**, 298, 28-32	2.8	2
231	The effect of the cross-gap alignment on magneto-transport in short period InAs/GaSb superlattices. *Physica B: Condensed Matter*, **2001**, 298, 344-347	2.8	1
230	MOVPE grown self-assembled and self-ordered InSb quantum dots in a GaSb matrix assessed by AFM, CTEM, HRTEM and PL. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2001**, 80, 112-115	3.1	20
229	Magneto-photoluminescence of AlGaN/GaN quantum wells. *Journal of Crystal Growth*, **2001**, 230, 487-491	1.6	4
228	Excitons with large binding energies in MgS/ZnSe/MgS and ZnMgS/ZnS/ZnMgS quantum wells. *Journal of Physics Condensed Matter*, **2001**, 13, 2317-2329	1.8	9
227	Internal self-ordering in In(Sb,As), (In,Ga)Sb, and (Cd,Zn,Mn)Se nano-agglomerates/quantum dots. *Applied Physics Letters*, **2001**, 79, 946-948	3.4	15

226	Atomic Self-ordering in Heteroepitaxially Grown Semiconductor Quantum Dots due to Relaxation of External Lattice Mismatch Strains. *Materials Research Society Symposia Proceedings*, **2001**, 696, 1		1
225	Atomic Self-Ordering in Heteroepitaxially Grown Semiconductor Quantum Dots Due to Relaxation of External Lattice Mismatch Strains. *Materials Research Society Symposia Proceedings*, **2001**, 707, 881		
224	Infrared single wavelength gas composition monitoring for metalorganic vapour-phase epitaxy. *Journal of Crystal Growth*, **2000**, 221, 166-171	1.6	16
223	Cyclotron resonance in an asymmetric electron-hole InAs/GaSb DHET structure. *Physica E: Low-Dimensional Systems and Nanostructures*, **2000**, 6, 660-663	3	3
222	A digital quantum Hall effect. *Physica E: Low-Dimensional Systems and Nanostructures*, **2000**, 6, 836-839	3	1
221	Designs for a quantum cascade laser using interband carrier extraction. *Physica E: Low-Dimensional Systems and Nanostructures*, **2000**, 7, 84-88	3	7
220	Intersubband transitions in InAs/GaSb superlattices in a parallel magnetic field. *Physica E: Low-Dimensional Systems and Nanostructures*, **2000**, 7, 93-96	3	3
219	MOVPE grown self-assembled Sb-based quantum dots assessed by means of AFM and TEM. *IEE Proceedings: Optoelectronics*, **2000**, 147, 209-215		11
218	The upgrade of the Oxford High Magnetic Field Laboratory. *IEEE Transactions on Applied Superconductivity*, **2000**, 10, 1552-1555	1.8	6
217	Metal-insulator oscillations in a two-dimensional electron-hole system. *Physical Review Letters*, **2000**, 85, 2364-7	7.4	23
216	A far infrared modulated photoluminescence (FIRM-PL) study of cyclotron resonance in a 2D electron gas in GaAs/AlxGa1-xAs heterojunctions. *Semiconductor Science and Technology*, **1999**, 14, 768-774	1.8	7
215	Searches for skyrmions in the limit of zero -factor. *Semiconductor Science and Technology*, **1998**, 13, 671-679	1.8	20
214	Skyrmions and composite fermions in the limit of vanishing Zeeman energy. *Journal of Physics Condensed Matter*, **1998**, 10, 11327-11335	1.8	3
213	Improved photoluminescence from electrochemically passivated GaSb. *Semiconductor Science and Technology*, **1997**, 12, 413-418	1.8	14
212	Optical studies of localized excitons in symmetric coupled quantum wells. *Superlattices and Microstructures*, **1997**, 21, 597-600	2.8	2
211	Photoconductivity studies of InAsP/InP heterostructures in applied magnetic and electric fields. *Semiconductor Science and Technology*, **1996**, 11, 34-38	1.8	3
210	Selective area epitaxy of InGaAs/InGaAsP quantum wells studied by magnetotransport. *Semiconductor Science and Technology*, **1996**, 11, 735-740	1.8	4
209	Magneto-optical studies of the type I/type II crossover and band offset in superlattices in magnetic fields up to 45 T. *Solid-State Electronics*, **1996**, 40, 69-74	1.7	1

208	Interface and layer thickness dependence of the effective mass in superlattices studied by high field cyclotron resonance. *Solid-State Electronics*, **1996**, 40, 181-184	1.7	12
207	Magneto-optical studies of compressively strained GaInPAlGaInP multiple quantum wells. *Solid-State Electronics*, **1996**, 40, 597-600	1.7	4
206	Growth of InAsGaSb strained layer superlattices. II. *Journal of Crystal Growth*, **1995**, 146, 495-502	1.6	24
205	Magneto-optical studies of the type-I/type-II crossover and band offset in ZnTe/Zn1-xMnxTe superlattices in magnetic fields up to 45 T. *Physical Review B*, **1995**, 52, 5269-5274	3.3	12
204	Magnetotransport in a pseudomorphic GaAs/Ga0.8In0.2As/Ga0.75Al0.25As heterostructure with a Si delta -doping layer. *Physical Review B*, **1995**, 52, 12218-12231	3.3	48
203	Influence of light on the confinement potential of GaAs/AlxGa1-xAs heterojunctions. *Physical Review B*, **1995**, 52, 2688-2696	3.3	25
202	Cyclotron-resonance measurements on p-type strained-layer Si1-xGex/Si heterostructures. *Physical Review B*, **1995**, 51, 13499-13502	3.3	10
201	Resonant cavity-enhanced (RCE) photodetector based on Ga(In)Sb for gas-sensing applications. *Semiconductor Science and Technology*, **1995**, 10, 1017-1021	1.8	8
200	A modified phenomenological description of the exchange interactions in dilute magnetic semiconductors. *Semiconductor Science and Technology*, **1995**, 10, 791-796	1.8	14
199	Temperature dependence of the band overlap in InAs/GaSb structures. *Physical Review B*, **1995**, 51, 1729-1734	3.3	12
198	An optically detected cyclotron resonance study of bulk GaAs. *Semiconductor Science and Technology*, **1994**, 9, 198-206	1.8	21
197	Electroluminescence out to 2.1 mu m observed in GaSb/InxGa1-xSb quantum wells grown by MOVPE. *Semiconductor Science and Technology*, **1994**, 9, 87-90	1.8	15
196	Collapse of high field magnetophonon resonance in GaAs-GaAlAs heterojunctions. *Physical Review Letters*, **1994**, 73, 589-592	7.4	21
195	Interband magneto-optical studies of resonant polaron coupling in CdTe/Cd1-xMnxTe quantum wells. *Physical Review B*, **1994**, 50, 7596-7601	3.3	10
194	[001]- and piezoelectric-[111]-oriented InAs/GaSb structures under hydrostatic pressure. *Physical Review B*, **1994**, 49, 16614-16621	3.3	22
193	Measurements of the effective mass and scattering times of composite fermions from magnetotransport analysis. *Physical Review Letters*, **1994**, 72, 1906-1909	7.4	158
192	Magneto-optical study of Ga1-xInxSb/GaSb strained-quantum-well structures: Miniband formation and valence-band structure. *Physical Review B*, **1994**, 49, 11210-11221	3.3	8
191	Observation of magnetic-field-induced semimetal-semiconductor transitions in crossed-gap superlattices by cyclotron resonance. *Physical Review B*, **1994**, 49, 10474-10483	3.3	22

190	One dimensional transport and gating of InAs/GaSb structures. *Superlattices and Microstructures*, **1994**, 15, 41	2.8	6
189	Optical and magnetotransport properties of semimetallic InAs/(In,Ga)Sb superlattices. *Physica B: Condensed Matter*, **1994**, 201, 271-279	2.8	16
188	Pulsed and high temperature superconducting magnet technology in Oxford. *Physica B: Condensed Matter*, **1994**, 201, 546-550	2.8	8
187	Direct observation of the semimetal to semiconductor transition in crossed band gap superlattices at magnetic fields of up to 150 T. *Solid-State Electronics*, **1994**, 37, 1027-1030	1.7	2
186	Cyclotron and intersubband resonance studies in [001] and piezoelectric [111] InAs/(Ga,In)Sb superlattices. *Solid-State Electronics*, **1994**, 37, 1227-1230	1.7	6
185	Growth of InAs/GaSb strained layer superlattices. I. *Journal of Crystal Growth*, **1994**, 145, 778-785	1.6	36
184	Variations of the hole effective masses induced by tensile strain in In1-xGaxAs(P)/InGaAsP heterostructures. *Physical Review B*, **1994**, 50, 7660-7667	3.3	8
183	Orientation and pressure dependence of the band overlap in InAs/GaSb structures. *Semiconductor Science and Technology*, **1994**, 9, 118-122	1.8	17
182	Effective mass and quantum lifetime in a Si/Si0.87Ge0.13/Si two-dimensional hole gas. *Applied Physics Letters*, **1994**, 64, 357-359	3.4	34
181	Cyclotron resonance to 100 mK of a GaAs heterojunction in the ultra-quantum limit. *Surface Science* , **1994**, 305, 33-41	1.8	11
180	Intrinsic quantum Hall effect in InAs/Ga1 InxSb crossed gap heterostructures in high magnetic fields. *Surface Science*, **1994**, 305, 156-160	1.8	13
179	Disappearance of magnetophonon resonance at high magnetic fields in GaAs/GaAlAs heterojunctions. *Surface Science*, **1994**, 305, 327-332	1.8	1
178	The design of quantum-confined Stark effect modulators for integration with 1.5 mu m lasers. *Semiconductor Science and Technology*, **1993**, 8, 1173-1178	1.8	8
177	Magnetotransport investigations at InSb and Hg1-xCdxTe bicrystals in tilted magnetic fields. *Semiconductor Science and Technology*, **1993**, 8, S168-S171	1.8	3
176	Devices and desires in the 2-4 mu m region based on antimony-containing III-V heterostructures grown by MOVPE. *Semiconductor Science and Technology*, **1993**, 8, S380-S385	1.8	21
175	The control and evaluation of blue shift in GaInAs/GaInAsP multiple quantum well structures for integrated lasers and Stark-effect modulators. *Semiconductor Science and Technology*, **1993**, 8, 1156-1165	1.8	4
174	Cyclotron resonance of high-mobility GaAs/AlGaAs (311) 2DHGs. *Semiconductor Science and Technology*, **1993**, 8, 1465-1469	1.8	20
173	Unusual behaviour of the Ge DX centre in GaAs: coexistence of two localized donor states. *Journal of Physics Condensed Matter*, **1993**, 5, 5001-5008	1.8	5

172	High-field magnetoresistance in GaAs/Ga0.7Al0.3As heterojunctions arising from elastic and inelastic scattering. *Physical Review B*, **1993**, 48, 5457-5468	3.3	19
171	Magnetoconductivity in a mesoscopic antidot array. *Physical Review B*, **1993**, 47, 7348-7353	3.3	18
170	Optical and transport properties of piezoelectric. *Physical Review B*, **1993**, 48, 17885-17891	3.3	6
169	Low-field magnetotransport study of localization in a mesoscopic antidot array. *Physical Review B*, **1993**, 47, 7354-7360	3.3	8
168	Superlattice modification of the valence-band spin splitting in InxGa1-xAs/GaAs superlattices up to 45 T. *Physical Review B*, **1993**, 48, 12323-12325	3.3	8
167	New phases of the 2D electron system in the ultra-quantum limit observed by cyclotron resonances. *Physical Review Letters*, **1993**, 70, 2150-2153	7.4	46
166	Piezoelectric effects in superlattices. *Semiconductor Science and Technology*, **1993**, 8, S367-S372	1.8	13
165	Unusual Behaviour of the DX-Centre in GaAs:Ge. *Japanese Journal of Applied Physics*, **1993**, 32, 218	1.4	6
164	Spin Split Cyclotron Resonance in a 2-D Electron System at Very High Magnetic Fields. *Journal of the Physical Society of Japan*, **1993**, 62, 1267-1271	1.5	11
163	Magneto-optical properties of Mn-based II□VI semimagnetic superlattices. *Physica B: Condensed Matter*, **1993**, 191, 156-170	2.8	6
162	A magneto-optical study of coupled quantum wells in strained GaInSb/GaSb. *Physica B: Condensed Matter*, **1993**, 184, 106-110	2.8	13
161	Cyclotron resonance measurements of the hole mass in [0 0 1] and [1 1 1] InxGa1□Sb/GaSb quantum wells. *Physica B: Condensed Matter*, **1993**, 184, 154-158	2.8	3
160	Optically detected cyclotron resonance of GaAs quantum wells. *Physica B: Condensed Matter*, **1993**, 184, 159-163	2.8	10
159	Ultra-high magnetic field cyclotron resonance of zero-gap InAs/GaSb superlattices. *Physica B: Condensed Matter*, **1993**, 184, 168-172	2.8	8
158	High-field magneto-resistance in GaAs-GaAlAs heterojunctions. *Physica B: Condensed Matter*, **1993**, 184, 197-201	2.8	3
157	Magnetotransport studies of GaSb/InAs crossed gap heterostructures in high magnetic fields. *Physica B: Condensed Matter*, **1993**, 184, 202-205	2.8	1
156	High magnetic field studies of the crossed-gap superlattice system InAs/GaSb. *Physica B: Condensed Matter*, **1993**, 184, 268-276	2.8	20
155	Magnetic-field- and temperature-dependent exciton delocalisation in a CdTe/Cd1□MnxTe superlattice. *Physica B: Condensed Matter*, **1993**, 184, 455-459	2.8	2

154	Superlattice dispersion in InGaAs/InGaAsP multi-quantum wells. *Semiconductor Science and Technology*, **1992**, 7, 493-497	1.8	6
153	Cyclotron resonance of the quasi-two-dimensional electron gas at Hg1-xCdxTe grain boundaries. *Semiconductor Science and Technology*, **1992**, 7, 511-515	1.8	3
152	Magnetotransport investigations and modelling of the Hg1-xCdxTe-anodic oxide accumulation system. *Semiconductor Science and Technology*, **1992**, 7, 810-817	1.8	9
151	Magnetotransport investigations of the quasi-two-dimensional electron system in Hg1-xCdxTe bicrystals in tilted magnetic fields. *Semiconductor Science and Technology*, **1992**, 7, 505-510	1.8	3
150	The pressure dependence of the effective mass in a GaAs/AlGaAs heterojunction. *Semiconductor Science and Technology*, **1992**, 7, 787-792	1.8	13
149	Magneto-optical studies of screened excitons in GaAs/AlxGa1-xAs modulation-doped quantum wells. *Physical Review B*, **1992**, 46, 4047-4052	3.3	12
148	Enhanced carrier densities and device performance in piezoelectric pseudomorphic high-electron mobility transistor structures. *Applied Physics Letters*, **1992**, 61, 1072-1074	3.4	23
147	Optically detected cyclotron resonance of GaAs quantum wells: Effective-mass measurements and offset effects. *Physical Review B*, **1992**, 46, 13394-13399	3.3	53
146	Saddle-point excitons and intraband (Gamma - Pi) mixing in strained-layer superlattices. *Physical Review B*, **1992**, 45, 4266-4273	3.3	8
145	Carrier-concentration-dependent polaron cyclotron resonance in GaAs heterostructures. *Physical Review B*, **1992**, 45, 4296-4300	3.3	49
144	Cyclotron resonance of both magnetopolaron branches for polar and neutral optical phonon coupling in the layer compound InSe. *Physical Review B*, **1992**, 45, 12144-12147	3.3	19
143	Cyclotron resonance in InAs/GaSb heterostructures. *Semiconductor Science and Technology*, **1992**, 7, 985-993	1.8	25
142	Intersubband resonant scattering in GaAs-Ga1-xAlxAs heterojunctions. *Physical Review B*, **1992**, 46, 12439-12447	3.3	72
141	Resonant magnetopolaron coupling to both polar and neutral optical phonons in the layer compound InSe. *Surface Science*, **1992**, 263, 654-658	1.8	3
140	Piezoelectric control of doping and band structure in the crossed gap system GaSb/InAs. *Surface Science*, **1992**, 263, 575-579	1.8	15
139	Interface studies of InAs/GaSb superlattices by Raman scattering. *Surface Science*, **1992**, 267, 176-180	1.8	25
138	Magneto-optical studies of CdTe:Cd1□MnxTe superlattices. *Surface Science*, **1992**, 267, 354-359	1.8	8
137	Valence band spin of semiconductor superlattices. *Surface Science*, **1992**, 267, 365-369	1.8	2

136	Optimization of the growth by MOVPE of strained GaSb/InAs double heterojunctions and superlattices on [111] GaAs substrates. *Journal of Crystal Growth*, **1992**, 124, 395-400	1.6	10
135	Strain and minibands in InGaAs?GaAs superlattices. *Superlattices and Microstructures*, **1991**, 9, 521-525	2.8	4
134	GaSb/InAs heterojunctions grown by MOVPE. *Journal of Crystal Growth*, **1991**, 107, 422-427	1.6	16
133	Valence band spin splitting in strained In0.18Ga0.82As/GaAs quantum wells. *Semiconductor Science and Technology*, **1991**, 6, 359-364	1.8	12
132	Photoluminescence at high pressures from highly strained MOVPE grown GaAs/GaSb/GaAs heterostructures. *Semiconductor Science and Technology*, **1991**, 6, 527-534	1.8	5
131	Magnetotransport of piezoelectric [111] oriented strained quantum wells. *Applied Physics Letters*, **1991**, 59, 659-661	3.4	16
130	High-pressure investigation of GaSb and Ga1-xInxSb/GaSb quantum wells. *Physical Review B*, **1991**, 43, 4994-5000	3.3	22
129	Hole-state reversal and the role of residual strain in (In,Ga)As-GaAs superlattices. *Physical Review B*, **1991**, 43, 12393-12400	3.3	10
128	Intraband and interband magneto-optics of p-type In0.18Ga0.82As/GaAs quantum wells. *Physical Review B*, **1991**, 43, 14124-14133	3.3	12
127	Miniband structure in InxGa1-xAs-GaAs strained-layer superlattices. *Physical Review B*, **1991**, 43, 2246-2254	3.3	15
126	Observation of optically detected magnetophonon resonance. *Physical Review Letters*, **1991**, 66, 794-797	7.4	39
125	GaSb/InAs heterojunctions grown by MOVPE: Effect of gas switching sequences on interface quality. *Journal of Crystal Growth*, **1991**, 110, 677-682	1.6	19
124	Photoluminescence of GaSb grown by metal-organic vapour phase epitaxy. *Semiconductor Science and Technology*, **1991**, 6, 45-53	1.8	65
123	Spectroscopic studies of miniband structure and band mixing in superlattices. *Superlattices and Microstructures*, **1990**, 8, 151-154	2.8	5
122	Evolution of the electronic states of coupled (In,Ga)As-GaAs quantum wells into superlattice minibands. *Physical Review B*, **1990**, 42, 3024-3029	3.3	17
121	Two-dimensional spin confinement in strained-layer quantum wells. *Physical Review B*, **1990**, 42, 9237-9240	3.3	69
120	Inter-subband scattering rates in GaAs-GaAlAs heterojunctions. *Semiconductor Science and Technology*, **1990**, 5, 1081-1087	1.8	23
119	Observation of magnetic excitons and spin waves in activation studies of a two-dimensional electron gas. *Physical Review B*, **1990**, 41, 1129-1134	3.3	174

118	□and X-miniband structure in GaAs?AlAs short period superlattices. *Surface Science*, **1990**, 228, 62-64	1.8	5
117	Strain reconstruction of the valence band in Ga1 □xInxSb/GaSb quantum wells. *Surface Science*, **1990**, 228, 270-274	1.8	30
116	Pressure dependence of light-hole transport in strained InGaAs/GaAs. *Surface Science*, **1990**, 229, 122-125	1.8	22
115	Bound state cyclotron resonance in modulation doped GaAs-AlxGa1□As quantum wells. *Surface Science*, **1990**, 229, 488-492	1.8	9
114	2D cyclotron resonance and magneto-polaron coupling to homopolar and lo phonons in the layered semiconductor InSe. *Surface Science*, **1990**, 229, 496-500	1.8	2
113	Influence of acoustic phonons on inter-subband scattering in GaAs-GaAlAs heterojunctions. *Semiconductor Science and Technology*, **1989**, 4, 885-888	1.8	34
112	Anomalies in the cyclotron resonance in high-mobility GaAs-Ga1-xAlxAs heterojunctions. *Physical Review B*, **1989**, 39, 10955-10962	3.3	47
111	GaAs/GaSb strained-layer heterostructures deposited by metalorganic vapor phase epitaxy. *Applied Physics Letters*, **1989**, 54, 1241-1243	3.4	27
110	Persistent photoconductivity in Ga0.49In0.51P/GaAs heterojunctions. *Journal of Applied Physics*, **1989**, 65, 2756-2760	2.5	18
109	GaSb/GaInSb quantum wells grown by metalorganic vapor phase epitaxy. *Applied Physics Letters*, **1989**, 54, 922-924	3.4	34
108	Temperature dependence of the cyclotron-resonance linewidth in GaAs-Ga1-xAlxAs heterojunctions. *Physical Review B*, **1989**, 39, 13302-13309	3.3	29
107	Magnetophonon resonance and remote phonon scattering in a GaInAs-AlInAs multi-quantum well. *Semiconductor Science and Technology*, **1989**, 4, 116-118	1.8	6
106	Shubnikov-de Haas effect of the quasi-two-dimensional electron system in InSb grain boundaries in tilted magnetic fields. *Semiconductor Science and Technology*, **1989**, 4, 747-753	1.8	6
105	Cyclotron phonon emission and electron energy loss rates in GaAs-GaAlAs heterojunctions. *Semiconductor Science and Technology*, **1989**, 4, 879-884	1.8	44
104	A transition from quantum well to superlattice behaviour in GaAs?AlAs short period superlattices. *Superlattices and Microstructures*, **1989**, 6, 51-54	2.8	4
103	Gamma -X mixing in the miniband structure of a GaAs/AlAs superlattice. *Physical Review Letters*, **1989**, 63, 2284-2287	7.4	58
102	Two-dimensional magnetopolaron coupling to both homopolar and longitudinal optic phonons in the layer compound InSe. *Journal of Physics Condensed Matter*, **1989**, 1, 7493-7498	1.8	11
101	Oscillatory behavior in the photoluminescence excitation and photoconductivity spectra of GaAs-AlAs superlattices. *Physical Review B*, **1989**, 39, 1219-1223	3.3	22

100	GaSb heterostructures grown by MOVPE. *Journal of Crystal Growth*, **1988**, 93, 70-78	1.6	41
99	Measurements of hot electron magnetophonon resonance in GaAs/GaAlAs heterostructures. *Solid-State Electronics*, **1988**, 31, 781-784	1.7	15
98	High magnetic field characterisation of (Hg, Cd)Te surface layers. *Journal of Crystal Growth*, **1988**, 86, 656-666	1.6	11
97	Pressure dependence study of the effective mass in Ga0.47In0.53As/InP heterojunctions. *Superlattices and Microstructures*, **1988**, 4, 201-206	2.8	8
96	The influence of a tilted magnetic field on the fractional quantum hall effect and the exchange enhancement of the spin splitting. *Surface Science*, **1988**, 196, 242-251	1.8	6
95	Cyclotron resonance of electrons in a narrow GaAs/(Ga,Al)As quantum well: Polaron effects and non-parabolicity. *Surface Science*, **1988**, 196, 429-436	1.8	41
94	Competition between LO and TO phonon scattering in GaAs/GaAlAs heterojunctions. *Surface Science*, **1988**, 196, 451-458	1.8	27
93	Observation of decoupled heavy and light holes in GaAs-Ga1-xAlxAs quantum wells by magnetoreflectivity. *Physical Review B*, **1988**, 38, 1323-1329	3.3	40
92	Exchange enhancement of the spin splitting in a GaAs-GaxAl. *Physical Review B*, **1988**, 37, 1294-1302	3.3	241
91	Carrier-concentation-dependent electron-LO-phonon coupling observed in GaAs-(Ga,Al)As heterojunctions by resonant-polaron cyclotron resonance. *Physical Review B*, **1988**, 38, 13133-13142	3.3	62
90	Experimental studies of the nu =1/5 hierarchy in the fractional quantum Hall effect. *Physical Review B*, **1988**, 38, 2200-2203	3.3	38
89	A study of parallel-field magnetoresistance of accumulation layers at anodic oxide films on n-(Hg, Cd)Te and the diamagnetic Shubnikov-de Haas effect. *Semiconductor Science and Technology*, **1988**, 3, 654-663	1.8	14
88	Growth of GaSb by MOVPE. *Semiconductor Science and Technology*, **1988**, 3, 315-320	1.8	76
87	A study of the conduction band non-parabolicity, anisotropy and spin splitting in GaAs and InP. *Semiconductor Science and Technology*, **1987**, 2, 568-577	1.8	88
86	Wavelength-dependent photoconduction effects on the second sub-band occupancy in (Al, Ga)As/GaAs heterojunctions. *Semiconductor Science and Technology*, **1987**, 2, 783-789	1.8	45
85	Modification of the electron-phonon interactions in GaAs-GaAlAs heterojunctions. *Physical Review Letters*, **1987**, 58, 77-80	7.4	142
84	Cyclotron-resonance study of nonparabolicity and screening in GaAs-Ga1-xAlxAs heterojunctions. *Physical Review B*, **1987**, 36, 4789-4795	3.3	67
83	Fractional quantum Hall effect in tilted magnetic fields. *Physical Review B*, **1987**, 36, 4528-4530	3.3	52

82	Transitions to confined states of the split-off band in GaAs-(Al,Ga)As multiple-quantum-well heterostructures. *Physical Review B*, **1987**, 35, 7784-7786	3.3	9
81	Millimeter and submillimeter detection using Ga1−xAlxAs/GaAs heterostructures. *Journal of Infrared, Millimeter and Terahertz Waves*, **1987**, 8, 793-802		7
80	Magneto-optics and strain effects in GaInAs?AlInAs and GaInAs?InP quantum wells. *Superlattices and Microstructures*, **1987**, 3, 69-74	2.8	1
79	Magneto-optical studies of GainAs?InP quantum wells. *Superlattices and Microstructures*, **1987**, 3, 471-475	2.8	17
78	Resonant 2D magnetopolarons in accumulation layers on n-Hg0.8Cd0.2Te. *Solid State Communications*, **1986**, 58, 833-838	1.6	24
77	Thermoelectric power of GaInAs-InP and GaInAs-AlInAs heterojunctions in a magnetic field. *Solid State Communications*, **1986**, 57, 377-380	1.6	7
76	Cyclotron resonance and screening effects in GaAs-GaAlAs heterojunctions. *Superlattices and Microstructures*, **1986**, 2, 319-322	2.8	33
75	High order fractional quantisation in a two dimensional system. *Solid State Communications*, **1986**, 60, 183-187	1.6	6
74	Thermoelectric power of GaAs-GaAlAs heterostructures in high magnetic fields. *Solid State Communications*, **1986**, 57, 381-384	1.6	14
73	Inter-band magneto-absorption in a Ga0.47In0.53As-Al0.48In0.52As quantum well. *Solid State Communications*, **1986**, 60, 83-86	1.6	8
72	Tilted field cyclotron resonance of accumulation layer electrons on n?Hg0.8Cd0.2Te. *Solid State Communications*, **1986**, 59, 819-823	1.6	2
71	Inter-band magneto-absorption in a Ga0.3In0.7As-InP strained layer superlattice. *Semiconductor Science and Technology*, **1986**, 1, 350-353	1.8	2
70	A study of n-type GaxIn1-xAsyP1-y-InP quantum wells. *Semiconductor Science and Technology*, **1986**, 1, 3-6	1.8	2
69	. *Journal of Physics C: Solid State Physics*, **1986**, 19, 77-92		32
68	Quantum transport in accumulation layers on Cd0.2Hg0.8Te. *Journal of Physics C: Solid State Physics* , **1986**, 19, 35-42		20
67	First observation of the quantum Hall effect in a Ga0.47In0.53As-InP heterostructure with three electric subbands. *Applied Physics Letters*, **1986**, 48, 712-714	3.4	52
66	Odd and even fractionally quantized states in GaAs-GaAlAs heterojunctions. *Surface Science*, **1986**, 170, 141-147	1.8	59
65	Measurements of thermoelectric power in two-dimensional systems. *Surface Science*, **1986**, 170, 298-303	1.8	11

64	Tilted field studies of Hg0.8Cd0.2Te accumulation layers. *Surface Science*, **1986**, 170, 409-415	1.8	5
63	Frequency shifted polaron coupling in GaInAs heterostructures. *Surface Science*, **1986**, 170, 542-548	1.8	20
62	Magneto-optics in GaAs-Ga1-xAlxAs quantum wells. *Physical Review B*, **1986**, 34, 4002-4009	3.3	217
61	Subband-Landau level coupling in a two-dimensional electron gas in tilted magnetic fields. *Journal of Physics C: Solid State Physics*, **1986**, 19, L107-L112		33
60	Double source photoconductivity of InP:Fe. *Physica Status Solidi A*, **1985**, 88, 347-353		2
59	Electron concentration dependent fractional quantisation in a two dimensional system. *Solid State Communications*, **1985**, 56, 173-176	1.6	13
58	The magnetophonon effect. *Progress in Quantum Electronics*, **1985**, 10, 1-75	9.1	85
57	Activated DC transport and infrared absorption in epitaxial n-InP. *Journal of Physics C: Solid State Physics*, **1985**, 18, 4021-4035		3
56	Limits on band discontinuities in GaAs-GaAlAs heterostructures deduced from optical photoresponse. *Journal of Physics C: Solid State Physics*, **1985**, 18, L891-L896		19
55	A study of the Cr and Fe deep acceptors in InP by the nuclear transmutation back doping technique. *Journal Physics D: Applied Physics*, **1985**, 18, 259-267	3	2
54	Shallow donor spectroscopy and polaron coupling in Ga0.47In0.53As. *Journal of Physics C: Solid State Physics*, **1985**, 18, L427-L431		18
53	The influence of alloy disorder on the k.p interaction in (GaIn)(AsP)/InP. *Journal of Physics C: Solid State Physics*, **1985**, 18, L443-L448		12
52	Cyclotron resonance linewidth in n-InSb at low temperatures. *Journal of Physics C: Solid State Physics*, **1985**, 18, 1495-1501		5
51	Phonon drag contribution to thermoelectric power in two-dimensional systems. *Journal of Physics C: Solid State Physics*, **1985**, 18, L695-L698		32
50	Frequency-shifted polaron coupling in Ga0.47In0.53As heterojunctions. *Physical Review Letters*, **1985**, 55, 883-886	7.4	87
49	Effect masses and non-parabolicity in GaxIn1-xAs. *Journal of Physics C: Solid State Physics*, **1985**, 18, 2667-2676		41
48	The k.p interaction in InP and GaAs from the band-gap dependence of the effective mass. *Journal of Physics C: Solid State Physics*, **1984**, 17, 4429-4442		70
47	Bulk and transfer doping effects in AlxGa1□As layers grown on semi-insulating GaAs substrates. *Applied Physics Letters*, **1984**, 44, 629-631	3.4	8

46	High magnetic field characterisation of MOCVD heterostructures and superlattices. *Journal of Crystal Growth*, **1984**, 68, 356-369	1.6	5
45	Structural and electronic properties of PbTe/Pb1−xSnxTe superlattices. *Surface Science*, **1984**, 142, 571-578	1.8	14
44	Two-dimensional magnetophonon resonance in GaInAs-InP and GaInAs-AlInAs heterojunctions and superlattices. *Surface Science*, **1984**, 142, 368-374	1.8	30
43	Cyclotron resonance and polaron effects in a two-dimensional electron gas in GaInAs. *Surface Science*, **1984**, 142, 380-387	1.8	30
42	An experimental determination of enhanced electron g-factors in GaInAs-A1InAs heterojunctions. *Solid State Communications*, **1983**, 45, 911-914	1.6	61
41	The electric sub-band structure of electron accumulation layers in InSe from Shubnikov-de Haas oscillations and inter-sub-band resonance. *Journal of Physics C: Solid State Physics*, **1983**, 16, 4285-4295		22
40	The cyclotron resonance linewidth in two-dimensional electron accumulation layers in InSe. *Journal of Physics C: Solid State Physics*, **1983**, 16, 2439-2448		11
39	Two-dimensional magnetophonon resonance. I. GaInAs-InP superlattices. *Journal of Physics C: Solid State Physics*, **1983**, 16, L573-L578		44
38	Two-dimensional magnetophonon resonance. II. GaInAs-AlInAs heterojunctions. *Journal of Physics C: Solid State Physics*, **1983**, 16, L579-L584		37
37	High magnetic field studies of the two-dimensional electron gas in GaInAs-InP superlattices. *Applied Physics Letters*, **1983**, 43, 293-295	3.4	15
36	Evidence for shallow bound states in PbTe. *Physical Review B*, **1983**, 28, 2244-2248	3.3	7
35	Optical investigations of the states in GaP:Ni. *Journal of Physics C: Solid State Physics*, **1982**, 15, 7355-7365		8
34	High field magneto-transport measurements in GaAs-GaAlAs multilayers. *Surface Science*, **1982**, 113, 290-294	1.8	20
33	Cyclotron resonance linewidth in a two-dimensional electron gas. *Surface Science*, **1982**, 113, 326-332	1.8	22
32	Two-dimensional behaviour due to electrons bound at defects in InSe. *Surface Science*, **1982**, 113, 339-346	1.8	23
31	Raman scattering from ion-implanted carriers in n-GaAs. *Solid-State Electronics*, **1982**, 25, 55-58	1.7	8
30	Quantum oscillations at a Ga0.47In0.53As?InP heterojunction interface. *Solid State Communications*, **1982**, 43, 825-828	1.6	35
29	Cyclotron resonance studies on bulk and two-dimensional conduction electrons in InSe. *Solid State Communications*, **1982**, 44, 379-383	1.6	100

28	Quantum transport in GaInAs-AlInAs heterojunctions, and the influence of intersubband scattering. *Solid State Communications*, **1982**, 43, 907-911	1.6	66
27	The influence of Landau level broadening on temperature dependent cyclotron resonance linewidths in semiconductors. *Solid State Communications*, **1982**, 41, 943-946	1.6	8
26	Shallow donor spectroscopy in GaxIn1-xAsyP1-y. *IEEE Journal of Quantum Electronics*, **1981**, 17, 145-149	2	6
25	Studies deep chromium acceptor levels in InP. *Journal of Physics C: Solid State Physics*, **1981**, 14, 2135-2146		16
24	On the Electronic g-Faetor in n-Type Silicon Inversion Layers. *Physica Status Solidi (B): Basic Research* , **1980**, 99, 237-242	1.3	29
23	The band structure of Pb1 Ge x Te above and below the structural phase transition. *Journal of Infrared, Millimeter and Terahertz Waves*, **1980**, 1, 485-499		2
22	An investigation of the valley splitting in n-channel silicon <100> inversion layers. *Solid State Communications*, **1980**, 34, 51-55	1.6	35
21	Two-dimensional conductivity in the contact regions of silicon MOSFETs. *Journal of Physics C: Solid State Physics*, **1980**, 13, L619-L622		2
20	A study of the energy loss mechanisms for hot electrons in CdTe and CdS from oscillatory photoconductivity and the magnetophonon effect. *Journal of Physics C: Solid State Physics*, **1980**, 13, 5215-5231		9
19	Cyclotron resonance and the magnetophonon effect in GaxIn1 AsyP1 . *Applied Physics Letters*, **1980**, 37, 178-180	3.4	80
18	Quantum transport in semiconductors. *Contemporary Physics*, **1980**, 21, 501-521	3.3	9
17	Raman scattering in InP1-xAsxalloys. *Journal of Physics C: Solid State Physics*, **1980**, 13, 899-910		41
16	Shubnikov-de Haas oscillations in n-channel silicon <100> MOSFETS in magnetic fields up to 35 T. *Solid State Communications*, **1979**, 31, 437-441	1.6	9
15	The magnetophonon effect in InAs1-xPx. *Journal of Physics C: Solid State Physics*, **1979**, 12, 1653-1664		18
14	A study of the deep acceptor levels of iron in InP. *Journal of Physics C: Solid State Physics*, **1979**, 12, 5145-5155		69
13	Evidence for a reduction in the momentum matrix element P2due to alloy disorder in InAp1-xPx. *Journal of Physics C: Solid State Physics*, **1979**, 12, 1641-1651		28
12	Size resonant scattering from a hard cylindrical potential observed in the magnetoresistance of InSb. *Journal of Physics C: Solid State Physics*, **1979**, 12, 2829-2837		3
11	Impurity-associated magnetophonon resonance in n-type silicon. *Journal of Physics C: Solid State Physics*, **1979**, 12, 5121-5143		4

10	An experimental determination of the effective masses for GaxIn1−xAsyP1−y alloys grown on InP. *Applied Physics Letters*, **1979**, 34, 492-494	3.4	112
9	The effects of high uniaxial stress on the far infra-red impurity spectra of high purity n- and p-type silicon. *Solid State Communications*, **1978**, 26, 11-15	1.6	16
8	The analysis of thermal activation of two-dimensional Shubnikov-De Haas conductivity minima and maxima. *Surface Science*, **1978**, 73, 106-115	1.8	21
7	An observation of central cell structure in magneto-impurity resonances in n-type InP. *Journal of Physics C: Solid State Physics*, **1978**, 11, L783-L787		5
6	The magnetophonon effect in p-type PbTe and Pb0.8Sn0.2Te. *Journal of Physics C: Solid State Physics*, **1977**, 10, L611-L615		6
5	Evidence for a contribution to the extrinsic photoconductive signal by hopping through excited states of the donors in silicon and CdTe. *Solid State Communications*, **1977**, 24, 55-60	1.6	23
4	Evidence for Anderson localisation in Landau level tails from the analysis of two-dimensional Shubnikov–de Haas conductivity minima. *Solid State Communications*, **1977**, 23, 341-345	1.6	55
3	An observation by photoconductivity of strain splitting of shallow bulk donors located near to the surface in silicon mos devices. *Solid State Communications*, **1976**, 20, 77-80	1.6	9
2	A time-dependent anomalous threshold in silicon MOS devices fabricated on high-resistivity substrates. *Journal Physics D: Applied Physics*, **1976**, 9, L109-L113	3	1
1	Energy relaxation mechanisms in n-type GaAs from magnetophonon spectroscopy. *Journal of Physics C: Solid State Physics*, **1976**, 9, 1253-1262		25